Abstracts

COM2 enhanced graded base SiGe technology for high speed applications (2002 [RFIC])

T. Ivanov, M. Carroll, S. Moinian, M. Mastrapasqua, A. Frei, A. Chen, C. King, A. Hamad, E. Martin, S. Shive, T. Esry, C. Lee, R. Johnson, T. Sorsch, K. Banoo, P. Smith and W. Cochran. "COM2 enhanced graded base SiGe technology for high speed applications (2002 [RFIC])." 2002 Radio Frequency Integrated Circuits (RFIC) Symposium 02. (2002 [RFIC]): 337-340.

The COM2 Enhanced Graded Base SiGe modular BiCMOS technology has been developed. It is based on the COM2 digital CMOS process. The technology achieves peak Ft=100 GHz, peak Fmax=101 GHz, peak /spl beta/=186 and BVcex=2.05 V. Ft-BVcex product of 205 and good across wafer uniformity are demonstrated.

❑ Return to main document.